

## **OXIDATION OF THIN METAL FILMS ON SILICON SUBSTRATE INVESTIGATED WITH ELECTROPHYSICAL METHODS**

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MOS structures are obtained by annealing of tin, tungsten, palladium and zinc thin films on silicon substrate in oxygen-containing atmosphere, and their high-frequency C–V, G–V and I–V characteristics are investigated. Similar peculiarities in energetic density of surface states for structures with non-stoichiometric oxides  $\text{SnO}_{2-x}$ ,  $\text{WO}_{3-x}$ ,  $\text{PdO}_x$  are found.